

Original document

MOS TRANSISTOR, SEMICONDUCTOR DEVICE AND THEIR MANUFACTURE

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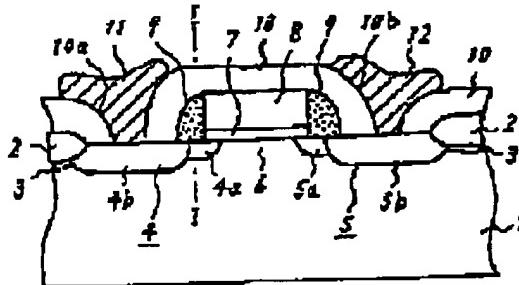
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Abstract of JP8139315

PURPOSE: To obtain a MOS transistor with an improved hot carrier resistance.

CONSTITUTION: In a transistor having a side surface of a gate electrode 8, a side surface of a gate insulation film 7, and a sidewall 9 formed in contact with one principal plane of a semiconductor substrate 1, the sidewall 9 comprises an oxide film in which nitrogen has been introduced to provide the peak of concentration distribution in a section normal to the principal plane of the semiconductor substrate 1 at the interface with the principal plane of the semiconductor substrate 1.



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